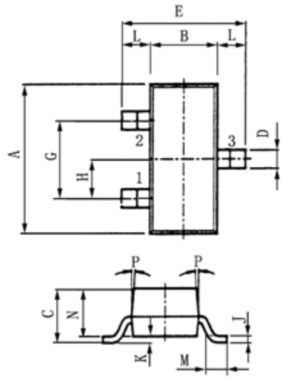
2SC536M(3DG536M)
2SC536KM(3DG536KM) 硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途:用于小信号一般放大电路。

Purpose: Small signal general purpose amplifier applications.

极限参数/Absolute Maximum Ratings(Ta=25℃)

参数符号 Symbol		数值 Rating	单位 Unit
V_{CBO}	3DG536M 3DG536KM	40 55	V
V_{CEO}	3DG536M 3DG536KM	30 50	V
V_{EBO}		5.0	V
I_C		100	mA
I_{CP}		300	mA
P_C		250	mW
T_j		150	℃
T_{stg}		-55～150	℃



单位 :mm

A	2.90±0.20
B	1.30+0.20/−0.15
C	1.30MAX
D	0.40+0.15/−0.05
E	2.40+0.30/−0.20
G	1.90±0.2
H	0.95±0.1
J	0.10+0.10/−0.05
K	0.00~0.10
L	0.55±0.1
M	0.20MIN
N	1.00+0.20/−0.10
P	7°

引脚：1:E 2:B 3:C

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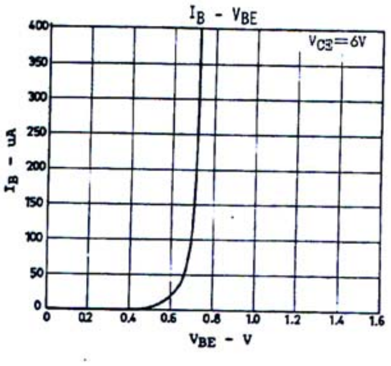
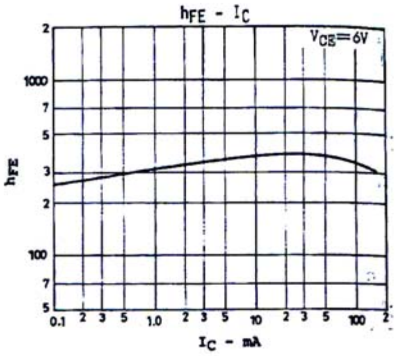
电性能参数/Electrical Characteristics(Ta=25℃)

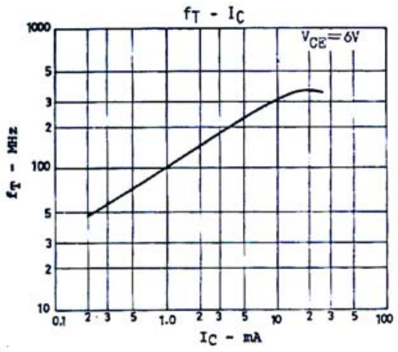
参数符号 Symbol	测试条件 Test Condition			数值 Rating		单位 Unit
			最小值 Min	典型值 Typ	最大值 Max	
I_{CBO}	V_{CB}=35V	I_E=0			1.0	μA
I_{EBO}	V_{EB}=4.0V	I_C=0			1.0	μA
h_{FE}	V_{CE}=6.0V	I_C=1.0mA	60		960	
$V_{CE(sat)}$	I_C=50mA	I_B=5.0mA			0.5	V
f_T	V_{CE}=6.0V	I_C=1.0mA		100		MHz
C_{ob}	V_{CB}=6.0V	I_E=0 f=1.0MHz		3.5		pF
C_c. $r_{bb'}$	V_{CB}=6.0V	I_c=1.0mA f=31.9MHz		250		pS

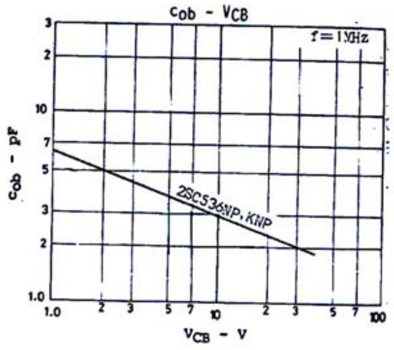
h_{FE}分档、印章/h_{FE} classifications、Marking:

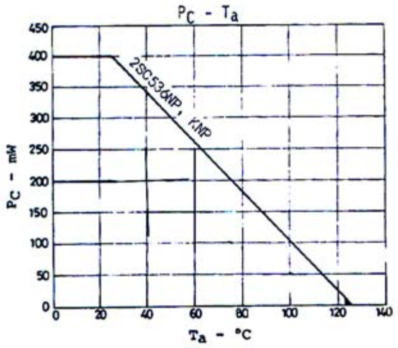
h_{FE}分档 h_{FE} Classifications	D	E	F	G	H
h_{FE}范围 h_{FE} Range	60～120	100～200	160～320	280～560	480～960
印章 Marking	H53D	H53E	H53F	H53G	H53H


IB - VBE
VCE=6V
IB - uA
400
350
300
250
200
150
100
50
0
0
0.2
0.4
0.6
0.8
1.0
1.2
1.4
1.6
VBE - V


hFE - IC
VCE=6V
hFE
2
1000
7
5
3
2
100
7
5
0.1
2
3
5
1.0
2
3
5
10
2
3
5
100
2
IC - mA


fT - IC
VCE=6V
fT - MHz
1000
5
3
2
100
5
3
2
10
0.1
2
3
5
1.0
2
3
5
10
2
3
5
100
IC - mA


Cob - VCB
f=1MHz
Cob - pF
3
2
10
7
5
3
2
1.0
1.0
2
3
5
7
10
2
3
5
7
100
2SC536NP, KNP
VCB - V


PC - Ta
2SC536NP, KNP
PC - mW
450
400
350
300
250
200
150
100
50
0
0
20
40
60
80
100
120
140
Ta - °C